



(11) **EP 1 361 614 B8**

(12) **CORRECTED EUROPEAN PATENT SPECIFICATION**

- (15) Correction information:  
**Corrected version no 1 (W1 B1)**  
**Corrections, see**  
**Bibliography INID code(s) 73**
- (48) Corrigendum issued on:  
**26.12.2012 Bulletin 2012/52**
- (45) Date of publication and mention of the grant of the patent:  
**07.11.2012 Bulletin 2012/45**
- (21) Application number: **02711222.6**
- (22) Date of filing: **24.01.2002**
- (51) Int Cl.:  
**H01L 21/04<sup>(2006.01)</sup> H01L 29/78<sup>(2006.01)</sup>**  
**H01L 21/316<sup>(2006.01)</sup>**
- (86) International application number:  
**PCT/JP2002/000512**
- (87) International publication number:  
**WO 2002/059980 (01.08.2002 Gazette 2002/31)**

(54) **SEMICONDUCTOR DEVICE MANUFACTURING METHOD**

HALBLEITERBAUELEMENTEHERSTELLUNGSVERFAHREN

PROCEDE DE FABRICATION D'UN DISPOSITIF SEMI-CONDUCTEUR

- (84) Designated Contracting States:  
**AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU**  
**MC NL PT SE TR**
- (30) Priority: **25.01.2001 JP 2001017680**
- (43) Date of publication of application:  
**12.11.2003 Bulletin 2003/46**
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